

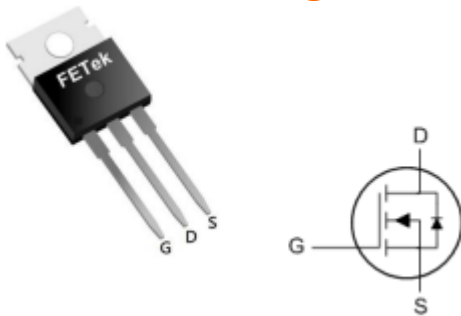
Description

The ECP0048 is the high cell density trench N-Ch MOSFETS, which provide excellent RDSON and gate charge for most of the Synchronous Rectification for AC/DC Quick Charger.

Product Summary

BVDSS	RDSON	ID
100V	9mΩ	80A

TO220 Pin Configuration



Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	100	V
V_{GS}	Gate-Source Voltage	±20	V
$I_D@T_C=25^{\circ}C$	Continuous Drain Current ^{1,6}	80	A
$I_D@T_C=100^{\circ}C$	Continuous Drain Current ^{1,6}	70.7	A
I_{DM}	Pulsed Drain Current ²	350	A
EAS	Single Pulse Avalanche Energy ³	61	mJ
I_{AS}	Avalanche Current	35	A
$P_D@T_C=25^{\circ}C$	Total Power Dissipation ⁴	188	W
T_{STG}	Storage Temperature Range	-55 to 175	°C
T_J	Operating Junction Temperature Range	-55 to 175	°C

Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction-Ambient ¹	---	58	°C/W
$R_{\theta JC}$	Thermal Resistance Junction-Case ¹	---	0.8	°C/W

**Electrical Characteristics** (T_J=25 °C, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =250uA	100	---	---	V
R _{DS(ON)}	Static Drain-Source On-Resistance ²	V _{GS} =10V, I _D =13.5A	---	6.6	9	mΩ
	Static Drain-Source On-Resistance ²	V _{GS} =4.5V, I _D =11.5A	---	8.7	12	
V _{GS(th)}	Gate Threshold Voltage	V _{GS} =V _{DS} , I _D =250uA	1.2	---	2.3	V
I _{DSS}	Drain-Source Leakage Current	V _{DS} =80V, V _{GS} =0V, T _J =25°C	---	---	1	uA
		V _{DS} =80V, V _{GS} =0V, T _J =55°C	---	---	5	
I _{GSS}	Gate-Source Leakage Current	V _{GS} =±20V, V _{DS} =0V	---	---	±100	nA
g _{fs}	Forward Transconductance	V _{DS} =5V, I _D =20A	---	85	---	S
Q _g	Total Gate Charge (10V)	V _{DS} =50V, V _{GS} =10V, I _D =13.5A	---	45	---	nC
Q _g	Total Gate Charge (4.5V)		---	19.3	---	
Q _{gs}	Gate-Source Charge		---	9.5	---	
Q _{gd}	Gate-Drain Charge		---	4.8	---	
T _{d(on)}	Turn-On Delay Time		---	10	---	
T _r	Rise Time	V _{DD} =50V, V _{GS} =10V, R _G =3Ω, I _D =13.5A	---	6.5	---	ns
T _{d(off)}	Turn-Off Delay Time		---	45	---	
T _f	Fall Time		---	7.5	---	
C _{iss}	Input Capacitance		---	3320	---	
C _{oss}	Output Capacitance	V _{DS} =50V, V _{GS} =0V, f=1MHz	---	605	---	pF
C _{rss}	Reverse Transfer Capacitance		---	20	---	

Diode Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I _S	Continuous Source Current ^{1,5,6}	V _G =V _D =0V, Force Current	---	---	80	A
V _{SD}	Diode Forward Voltage ²	V _{GS} =0V, I _S =1A, T _J =25°C	---	---	1.1	V
t _{rr}	Reverse Recovery Time	I _F =13.5A, di/dt=100A/μs,	---	33	---	nS
Q _{rr}	Reverse Recovery Charge	T _J =25°C	---	150	---	

Note:

- 1.The data tested by surface mounted on a 1 inch² FR-4 board with 2OZ copper.
- 2.The data tested by pulsed , pulse width ≤ 300us , duty cycle ≤ 2%
- 3.The EAS data shows Max. rating. The test condition is V_{DD}=25V, V_{GS}=10V, L=0.3mH, I_{AS}=35A
- 4.The power dissipation is limited by junction temperature
- 5.The data is theoretically the same as I_D and I_{DM}, in real applications, should be limited by total power dissipation.
- 6.The maximum current rating is package limited.

Typical Characteristics

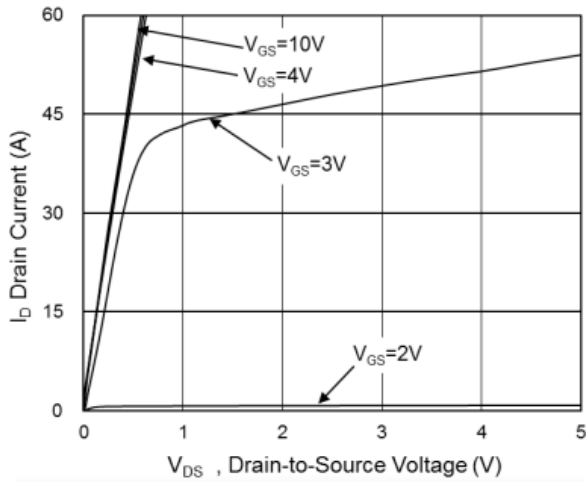


Fig.1 Typical Output Characteristics

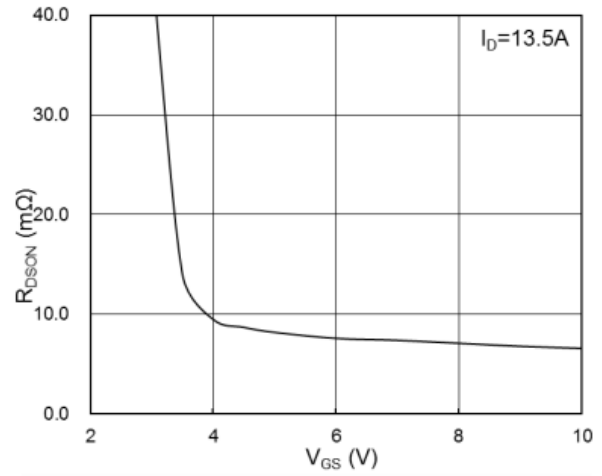


Fig.2 On-Resistance vs. G-S Voltage

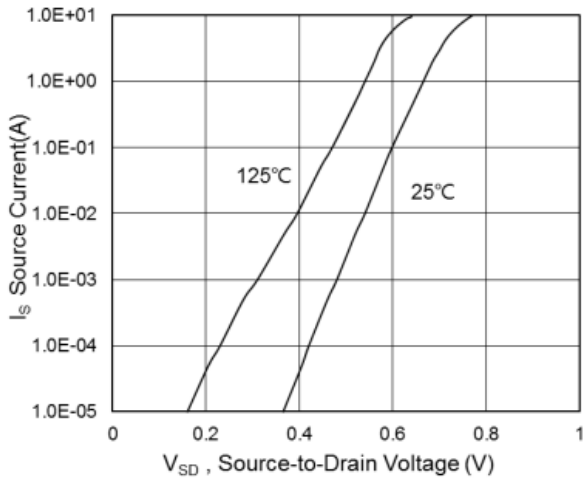


Fig.3 Source-Drain Forward Characteristics

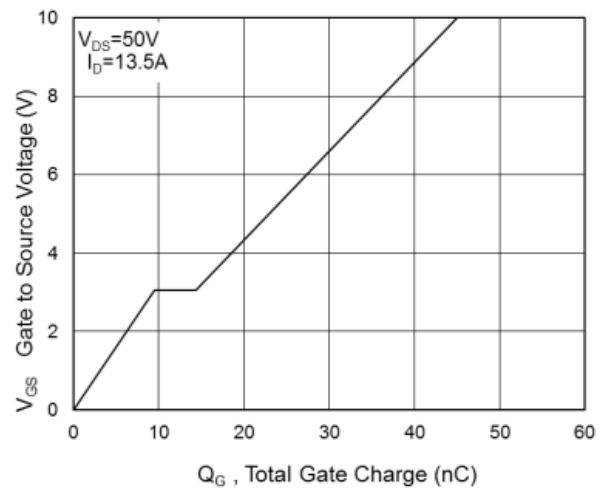


Fig.4 Gate-Charge Characteristics

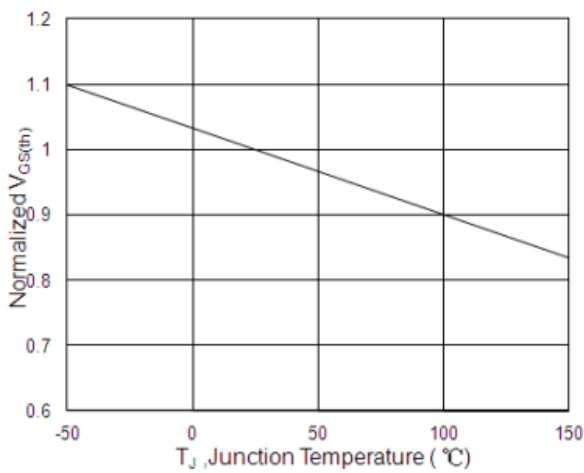


Fig.5 Normalized $V_{GS(th)}$ vs. T_J

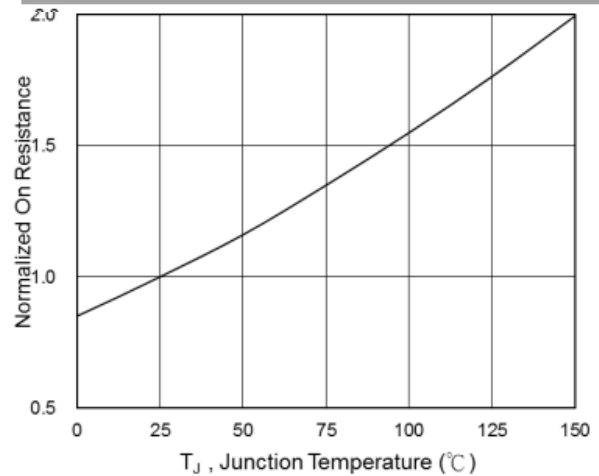


Fig.6 Normalized $R_{DS(on)}$ vs. T_J

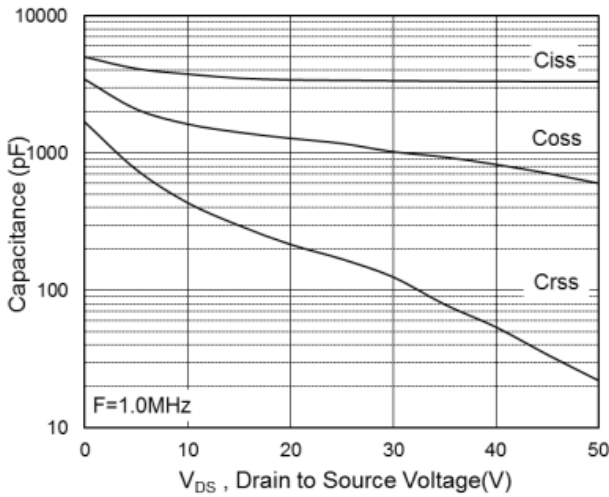


Fig.7 Capacitance

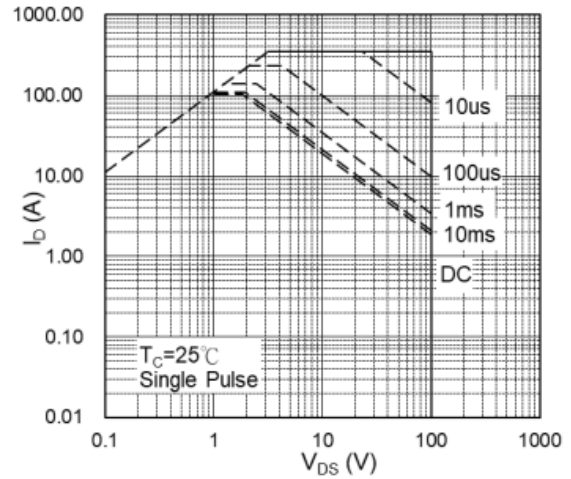


Fig.8 Safe Operating Area

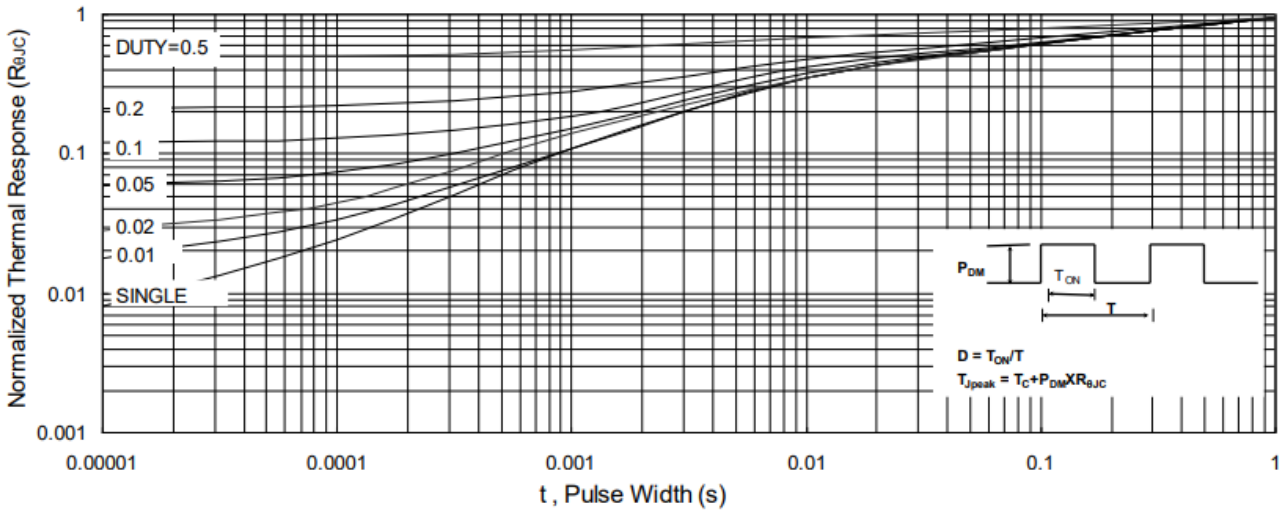


Fig.9 Normalized Maximum Transient Thermal Impedance

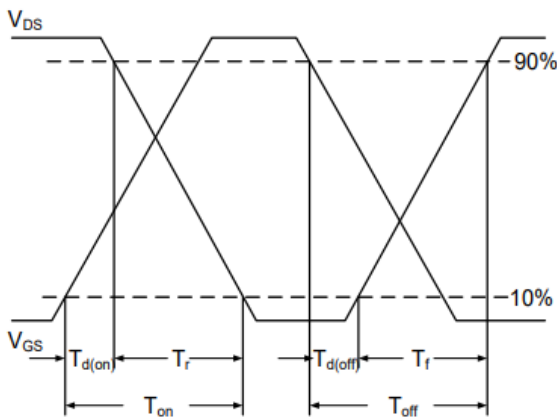


Fig.10 Switching Time Waveform

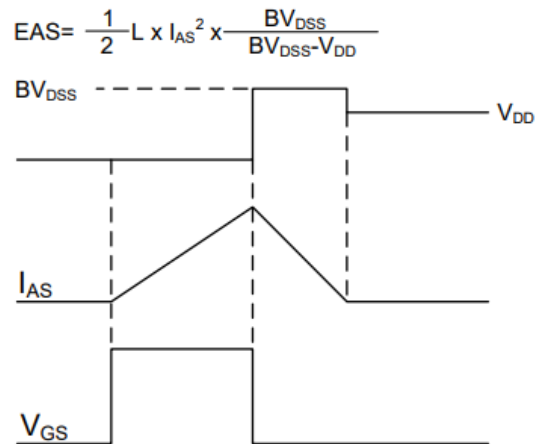
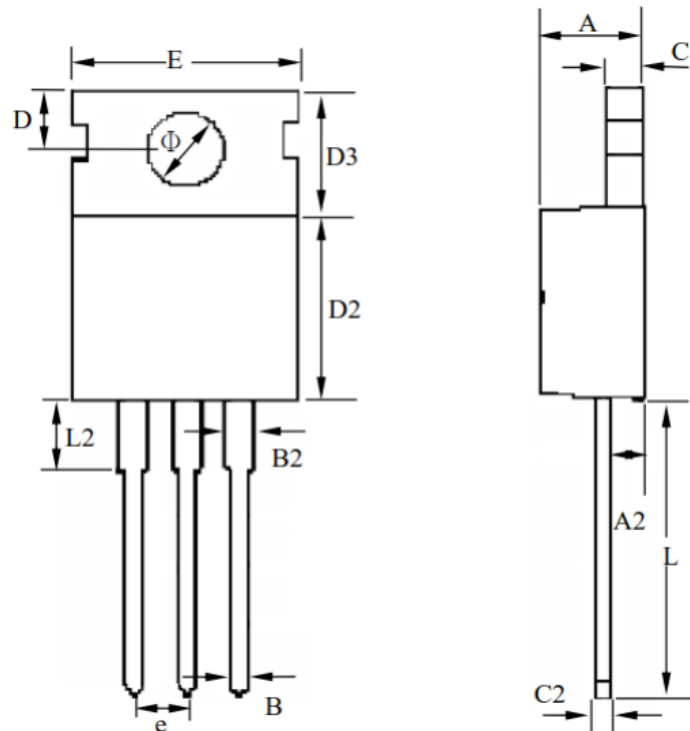


Fig.11 Unclamped Inductive Switching Waveform

TO220 Package Outline Dimensions



SYMBOLS	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	4.25	--	4.80	0.167	--	0.189
A2	2.20	--	2.92	0.087	--	0.115
B	0.70	--	0.91	0.028	--	0.036
B2	1.15	--	1.77	0.045	--	0.070
C	1.20	--	1.40	0.047	--	0.055
C2	0.45	--	0.61	0.018	--	0.024
D	2.54	--	3.00	0.100	--	0.118
D2	8.39	--	9.47	0.330	--	0.373
D3	6.30	--	6.70	0.248	--	0.264
E	9.70	--	10.36	0.382	--	0.408
L	12.75	--	14.40	0.502	--	0.567
L2	2.45	--	4.05	0.096	--	0.159
Φ	3.50	--	3.80	0.138	--	0.150
e	--	2.54	--	--	0.100	--